**Product / Process Change Notice**

**Parts Affected:**

Chip process, CP775, P-channel MOSFETs, wafers and bare die.

**Extent of Change:**

The CP775 wafer process has been discontinued and is being replaced with the CP802 wafer process. See Figures 1 and 2 for details.

**Reason for Change:**

The CP775 wafer process has been replaced in order to enhance manufacturing process controls and device performance. This change will help ensure an undisrupted supply of product.

**Effect of Change:**

The CP802 wafer process meets all electrical specifications of the individual devices listed on the following page.

**Qualification:**

|  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- |
|  |  | P/N: | CP802X Chip Process |  | Package: | TO-220 |
|  |  |  |  |  |  |  |
| **No.** | | **Test** | **Conditions** (Reference standards are in bold) | **Qty** | **Pass/Fail** | **Test Results** |
| **1** | | **Device Life Tests** | | | | |
|  | A | **High Temperature Gate Bias (HTGB)** | T=150°C, t = 1000 hours 100% V\_GS  Negative Bias **JESD22-A108** | 77 | Pass | 77/77 |
|  | B | **High Temperature Gate Bias (HTGB)** | T=150°C, t = 1000 hours 100% V\_GS  Positive Bias **JESD22-A108** | 77 | Pass | 77/77 |
|  | C | **High Temperature Reverse Bias (HTRB)** | T=150°C, t = 1000 hours 100% V\_DS **JESD22-A108** | 77 | Pass | 77/77 |

**Effective Date of Change:**

Existing inventory of chip process CP775 will be shipped until depleted.

**Sample Availability:**

Please contact your salesperson or manufacturer’s representative for samples.

**Figure 1: CP775 Chip Geometry (Discontinued) Figure 2: CP802 Chip Geometry**



Wafer Diameter: 8 inch

Die Size: 90 x 60 mils

Die Thickness: 5.5 mils

Bond Pad Size (Gate): 14.1 x 18.8 mils

Bond Pad Size (Source): 88 x 52 mils

Topside Metal: Al (40,000Å)

Backside Metal: Ti/Ni/Ag (1,000Å/3,000Å/10,000Å)

Wafer Diameter: 8 inch

Die Size: 83.5 X 57.1 mils

Die Thickness: 5.5 mils

Bond Pad Size (Gate): 5.5 x 5.5 mils

Bond Pad Size (Source 1): 39.1 x 54.1 mils

Bond Pad Size (Source 2): 39.1 X 54.1 mils

Topside Metal: Al-Cu (40,000Å)

Backside Metal: Ti/Ni/Ag (1,000Å/3,000Å/10,000Å)

**Part Numbers Affected:**

|  |  |
| --- | --- |
| CWDM3011P | CP775-CWDM3011P-CT |
|  | CP775-CWDM3011P-CM |
|  | CP775-CWDM3011P-WN |

As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor’s Product/Process Change Notification (PCN).

|  |  |
| --- | --- |
| Company Name: |  |
| Address: |  |
|  |
|  |
| Printed Name: |  |
| Title: |  |
| Signature: |  |
| Date: |  |